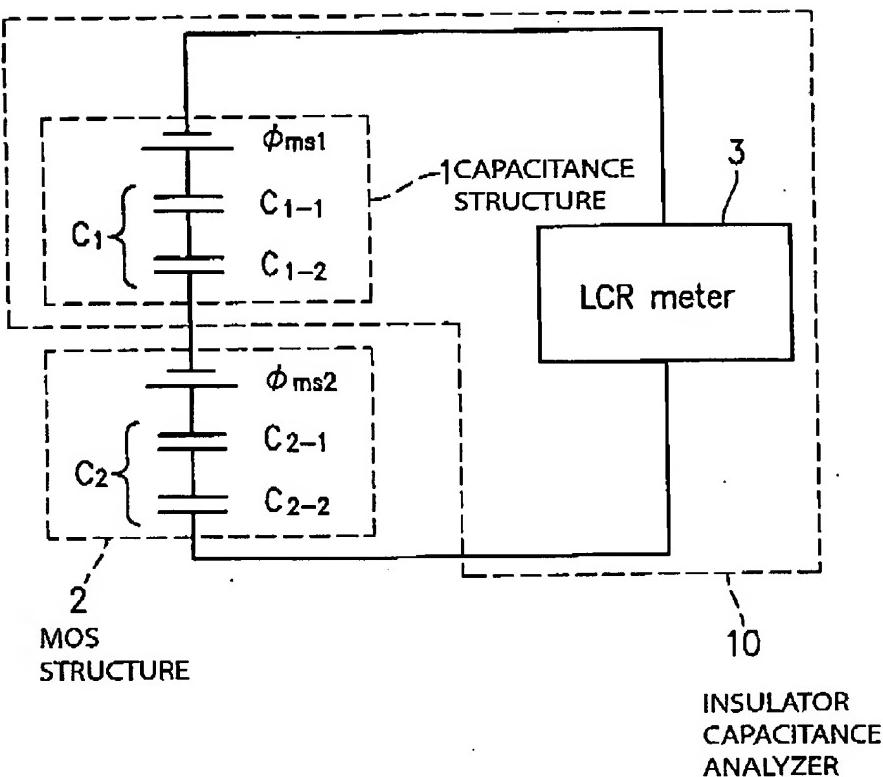


FIG. 1



SN 10/003,258/Sheet 2 of 9  
Atty. Dkt.: 829-593  
REPLACEMENT SHEET

*FIG.2*

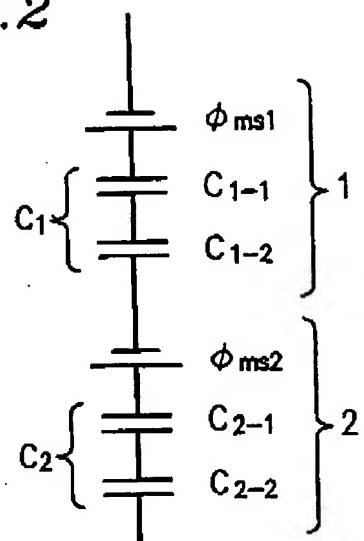
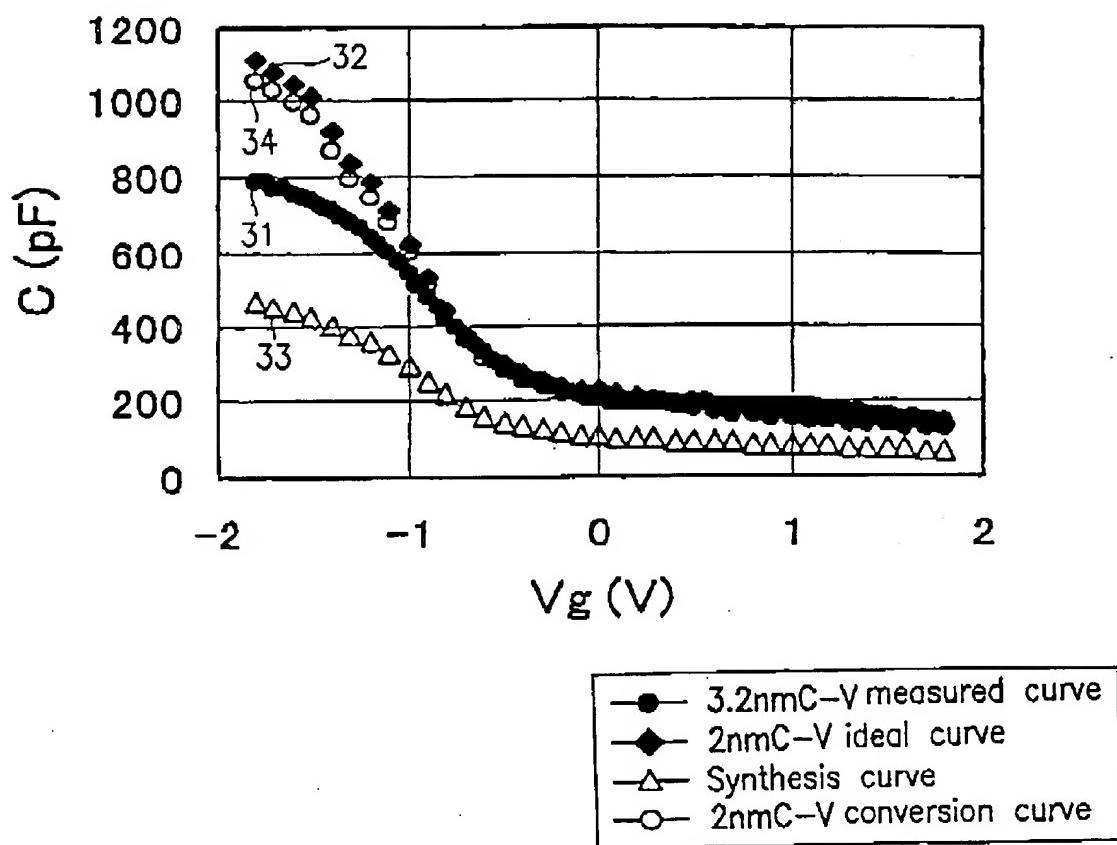
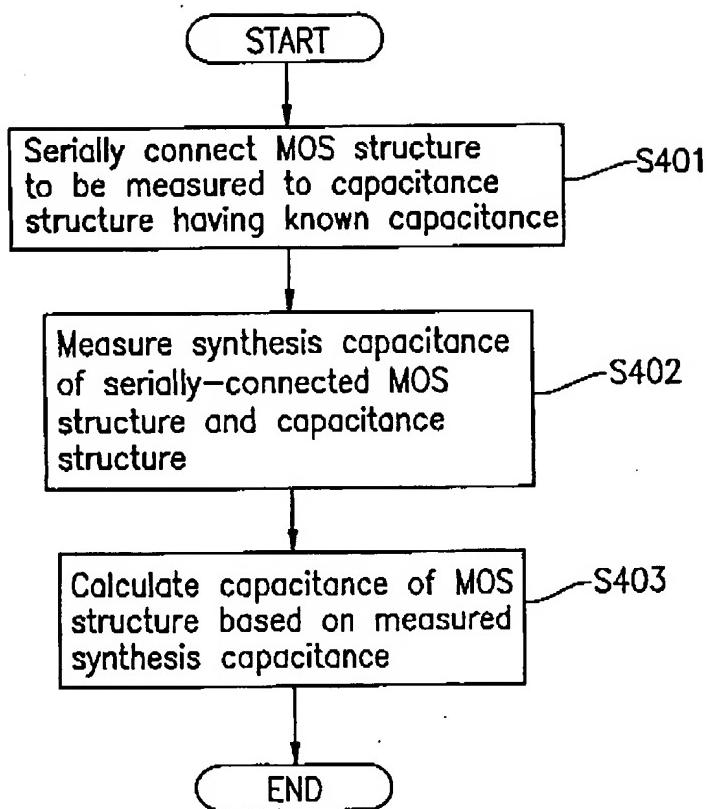


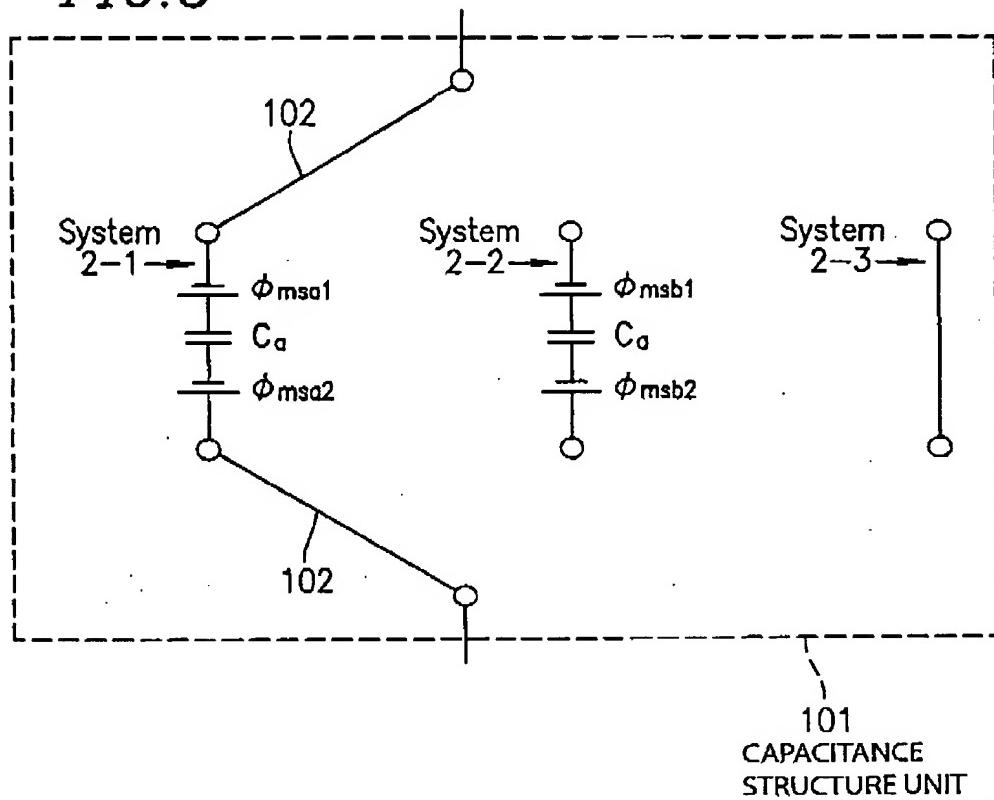
FIG. 3

## NMOS C-V Characteristics



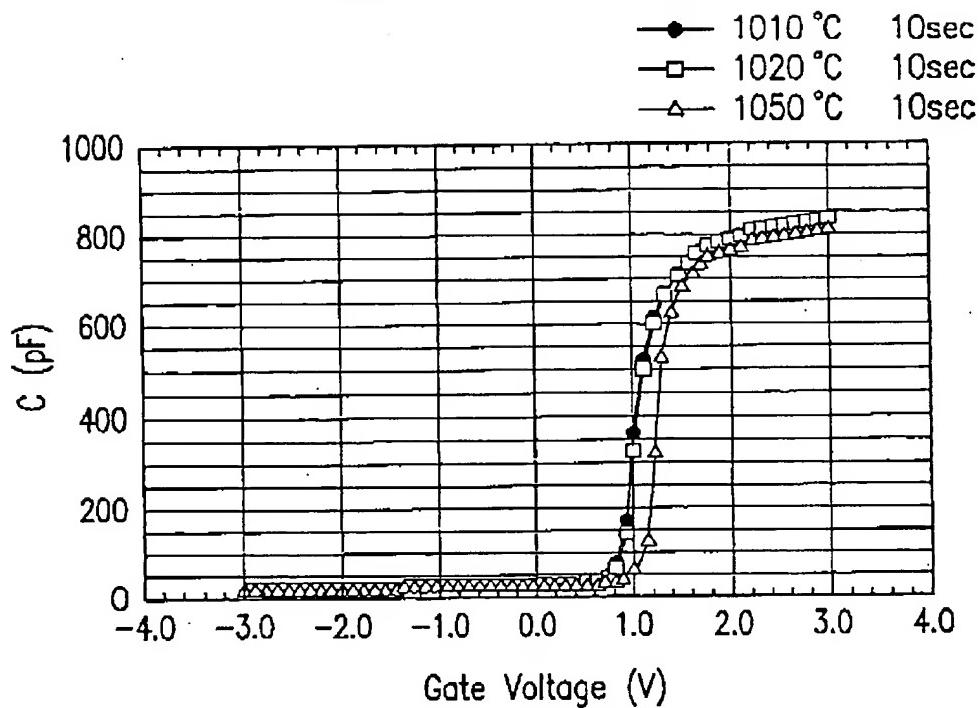
*FIG. 4*



*FIG. 5*

Inventor: OHMINAMI  
SN 10/003,258/Sheet 6 of 9  
Atty. Dkt.: 829-599  
REPLACEMENT SHEET

**FIG. 6**  
PMOS C-V Characteristics



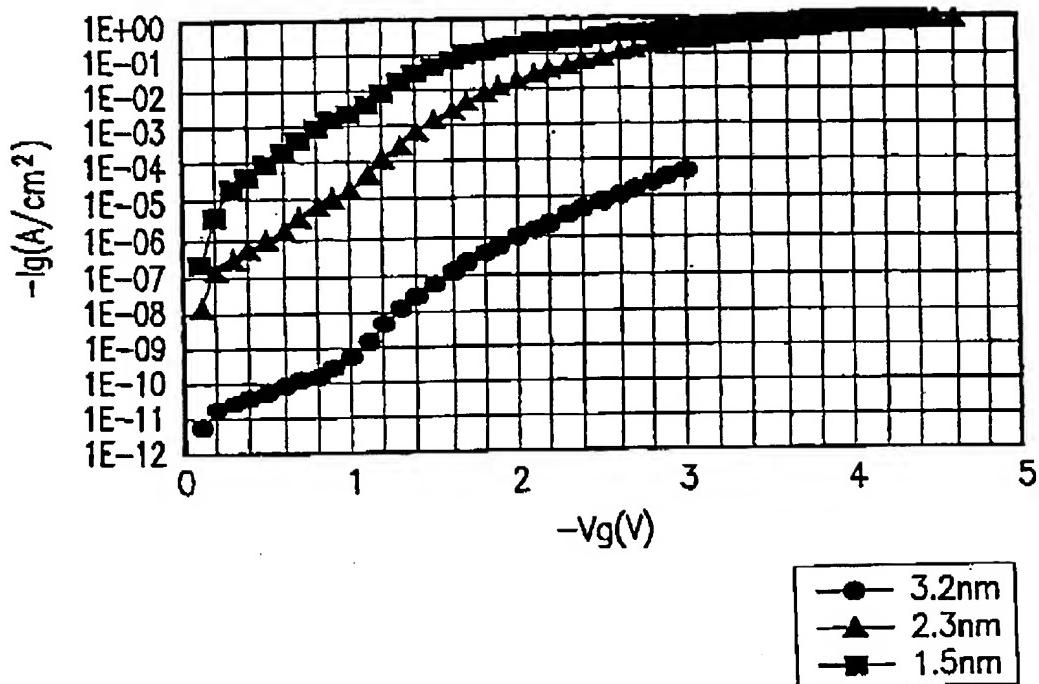
Active Area: 9E-4cm<sup>2</sup>  
w/o Well Imp.  
Gate SiON: NO/N<sub>2</sub>

poly Si: 200nm  
P+Imp.: BF<sub>2</sub>

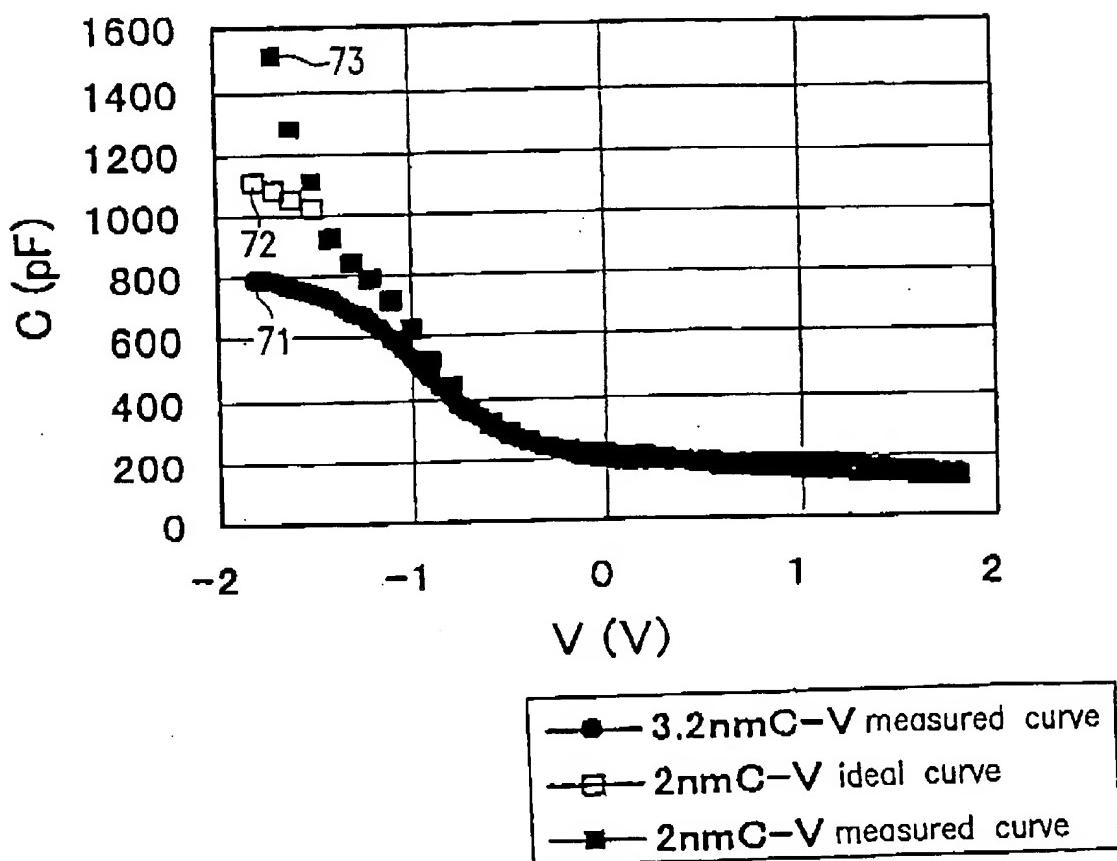
Inventor: OHM/NAM  
SN 10/003,258/Sheet 7 of 8  
Atty. Dkt.: 829-593  
REPLACEMENT SHEET

*FIG. 7*

NMOS I-V Characteristics



*FIG. 8* (PRIOR ART)  
NMOS C-V Characteristics



*FIG. 9* (PRIOR ART)